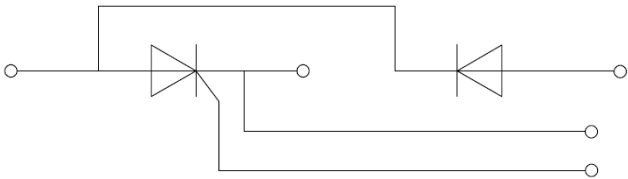




°C		



	°C			
				°C
				°C



	°C					
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FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)
 $P_{T(AV)}/P_{F(AV)}(W)$

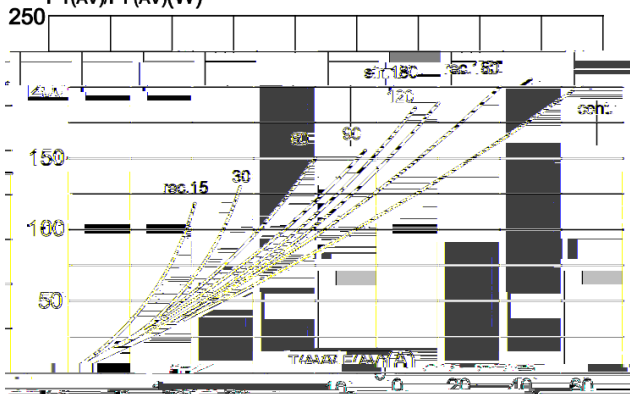


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)
 $R_{th(j-c)}(^{\circ}C/W)$

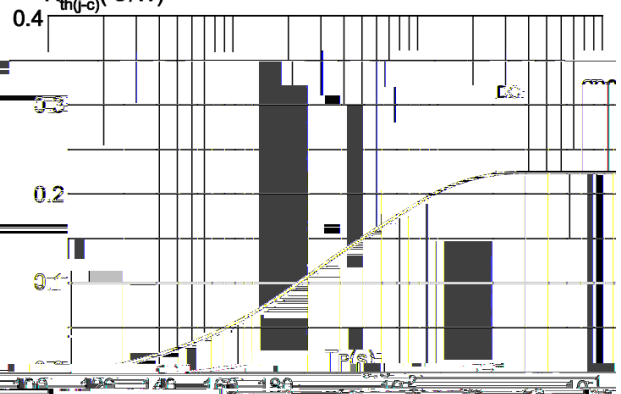


FIG.3: Forward characteristics
(per thyristor or diode)
 $I_F(A)/T(^{\circ}C)$

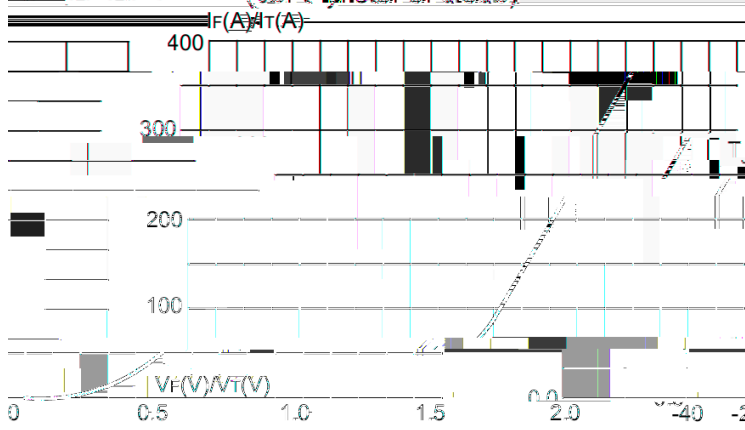
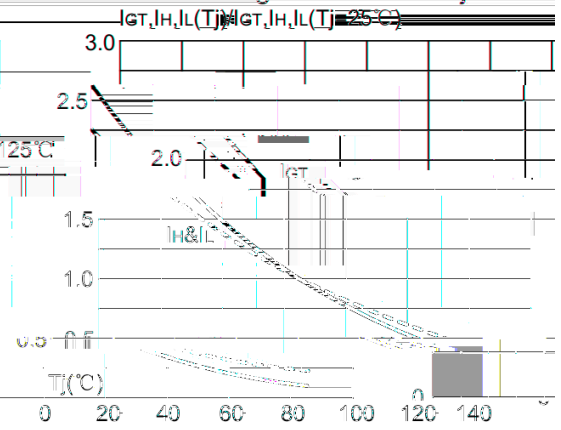


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature
 $I_{GT}, I_H, I_L(T)/I_{GT}, I_H, I_L(T_{25^{\circ}C})$



case temperature de)

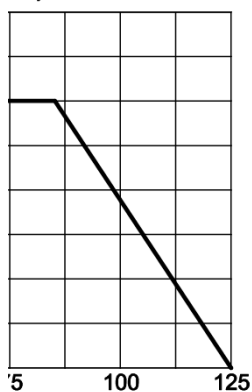


FIG.5 Gate trigger characteristics

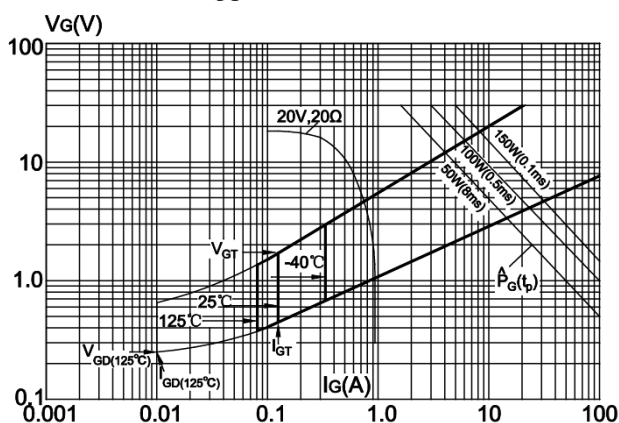


FIG.6: Forward current vs.
 $I_{F(AV)}(A)$ (per thyristor or diode)

